AUTOMOTIVE GRADE

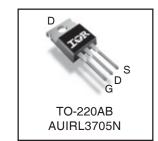
International

AUIRL3705N

HEXFET[®] Power MOSFET

Features

- Advanced Planar Technology
- Logic-Level Gate Drive
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



G	D	S
Gate	Drain	Source

Description Specifically de

Specifically designed for Automotive applications, this Cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low onresistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	89©	
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	63	A
I _{DM}	Pulsed Drain Current ①	310	
P _D @T _C = 25°C	Power Dissipation	170	
	Linear Derating Factor	101	W/°C
V _{GS}	Gate-to-Source Voltage	±16	V
E _{AS}	Single Pulse Avalanche Energy 2	340	mJ
I _{AR}	Avalanche Current ①	46	A
E _{AR}	Repetitive Avalanche Energy ①	17	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
TJ	Operating Junction and	-55 to + 175	
T _{STG}	Storage Temperature Range		°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Тур.	Max.	Units
R _{eJC}	Junction-to-Case		0.90	
R _{ecs}	Case-to-Sink, Flat, Greased Surface	0.50		
R _{0JA}	Junction-to-Ambient		62	°C/W

HEXFET[®] is a registered trademark of International Rectifier. *Qualification standards can be found at http://www.irf.com/ www.irf.com

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55			V	$V_{GS} = 0V, I_D = 250 \mu A$
$\Delta V_{(BR)DSS} / \Delta T_J$	Breakdown Voltage Temp. Coefficient		0.056		V/°C	Reference to 25° C, I _D = 1mA
				0.010		V _{GS} = 10V, I _D = 46A ④
R _{DS(on)}	Static Drain-to-Source On-Resistance			0.012	Ω	$V_{GS} = 5.0V, I_{D} = 46A$ (4)
				0.018		$V_{GS} = 4.0V, I_{D} = 39A$ (4)
V _{GS(th)}	Gate Threshold Voltage	1.0		2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
gfs	Forward Transconductance	50			S	$V_{DS} = 25V, I_{D} = 46A$ (5)
I _{DSS}	Drain-to-Source Leakage Current			25	μA	$V_{DS} = 55V, V_{GS} = 0V$
				250		$V_{DS} = 44V, V_{GS} = 0V, T_{J} = 150^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage			100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage			-100		V _{GS} = -16V

Dynamic Electrical Characteristics @ $T_J = 25^{\circ}C$ (unless otherwise specified)

	•	•			-	
Qg	Total Gate Charge			98		I _D = 46A
Q _{gs}	Gate-to-Source Charge			19	nC	$V_{DS} = 44V$
Q _{gd}	Gate-to-Drain ("Miller") Charge			49		V_{GS} = 5.0V,See Fig 6 and 13 \oplus
t _{d(on)}	Turn-On Delay Time		12			$V_{DD} = 28V$
t _r	Rise Time		140			I _D = 46A
t _{d(off)}	Turn-Off Delay Time		37		ns	$R_G = 1.8\Omega, V_{GS} = 5.0V$
t _f	Fall Time		78			$R_D = 0.59\Omega$, See Fig.10 ④
L _D	Internal Drain Inductance		4.5		nH	Between lead, 6mm (0.25in.)
L _S	Internal Source Inductance		7.5			from package
C _{iss}	Input Capacitance		3600			$V_{GS} = 0V$
C _{oss}	Output Capacitance		870		pF	$V_{DS} = 25V$
C _{rss}	Reverse Transfer Capacitance		320			f = 1.0MHz, See Fig.5

Diode Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions
I _S	Continuous Source Current			89 ©		MOSFET symbol
	(Body Diode)			090		showing the
I _{SM}	Pulsed Source Current			310		integral reverse
	(Body Diode) ①			310		p-n junction diode.
V _{SD}	Diode Forward Voltage			1.3	V	$T_J = 25^{\circ}C, I_S = 46A, V_{GS} = 0V$ (4)
t _{rr}	Reverse Recovery Time		94	140	ns	T _J = 25°C, I _F = 46A
Q _{rr}	Reverse Recovery Charge		290	440	nC	di/dt = 100A/µs ④
t _{on}	Forward Turn-On Time	Intrinsic	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)			

Notes:

- $\odot\,$ Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- $@~V_{DD}$ = 25V, starting T_J = 25°C, L = 320µH, R_G = 25 Ω , I_{AS} = 46A. (See Figure 12)

- ⑤ Calculated continuous current based on maximum allowable junction temperature. for recommended current-handling of the package refer to Design tip # 93-4

Qualification Information[†]

		Automotive				
			(per AEC-Q101) ^{††}			
Qualification Level		qualification.	This part number(s) passed Automotive R's Industrial and Consumer qualification by extension of the higher Automotive level.			
Moisture Sensitivity Level		3L-TO-220	N/A			
	Machine Model	Class M4(+/- 800V) ^{†††}				
		(per AEC-Q101-002)				
FOD	Human Rady Madal	Class H1C(+/- 2000V) ^{†††}				
ESD	Human Body Model	(per AEC-Q101-001)				
	Charged Device Medel		Class C5(+/- 2000V) ^{†††}			
	Charged Device Model		(per AEC-Q101-005)			
RoHS Complia	RoHS Compliant		Yes			

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

t Exceptions to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage

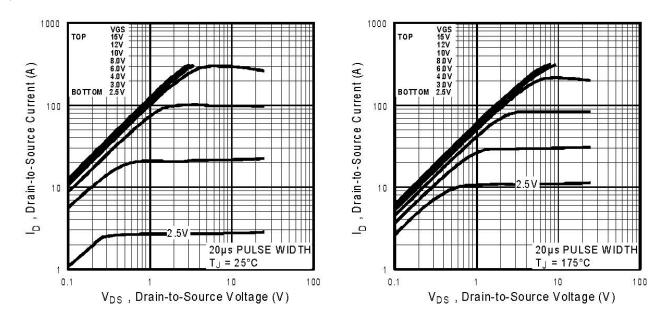
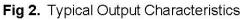


Fig 1. Typical Output Characteristics



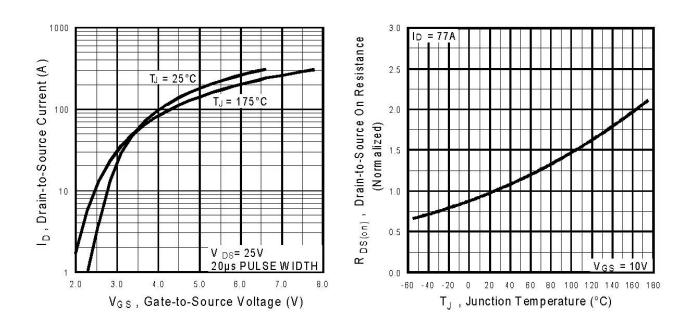
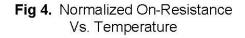


Fig 3. Typical Transfer Characteristics



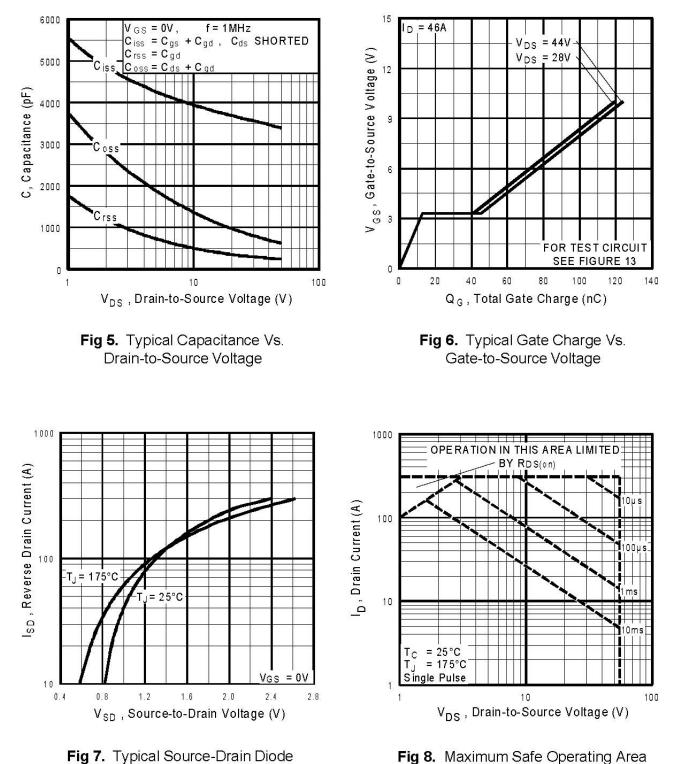
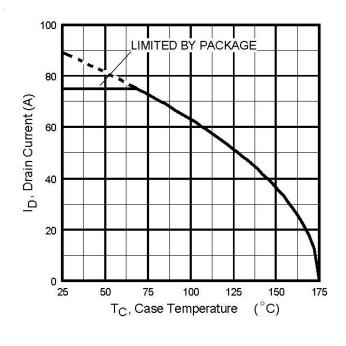
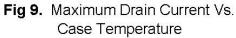


Fig 8. Maximum Safe Operating Area

Forward Voltage





 V_{DS} R_{D} V_{GS} D.U.T. R_{G} D.U.T. T_{DD} T_{DD} T_{DD} T_{DD} T_{DD} T_{DD} T_{DD} T_{DD} T_{DD}

Fig 10a. Switching Time Test Circuit

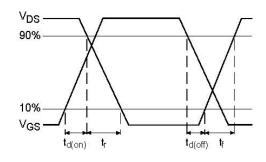


Fig 10b. Switching Time Waveforms

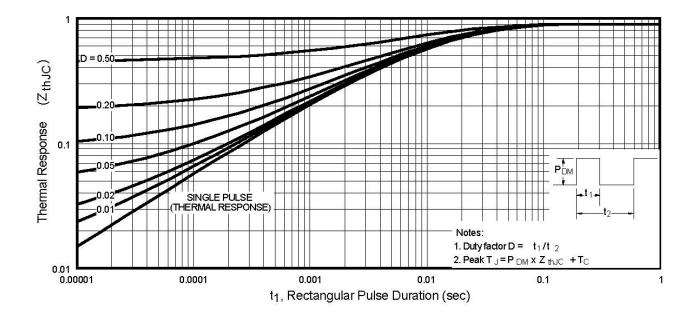


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

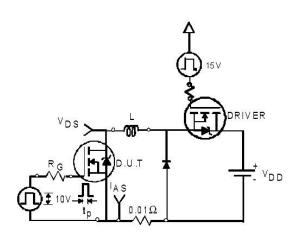


Fig 12a. Unclamped Inductive Test Circuit

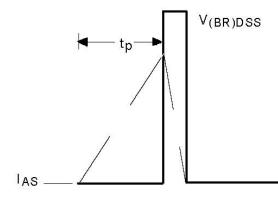


Fig 12b. Unclamped Inductive Waveforms

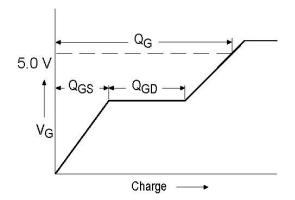
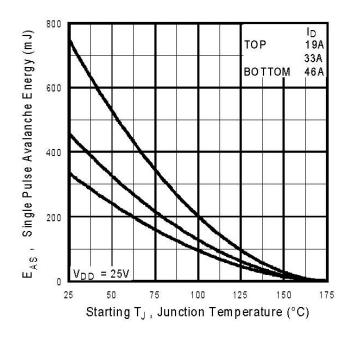
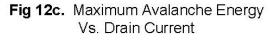


Fig 13a. Basic Gate Charge Waveform





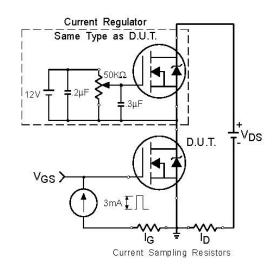
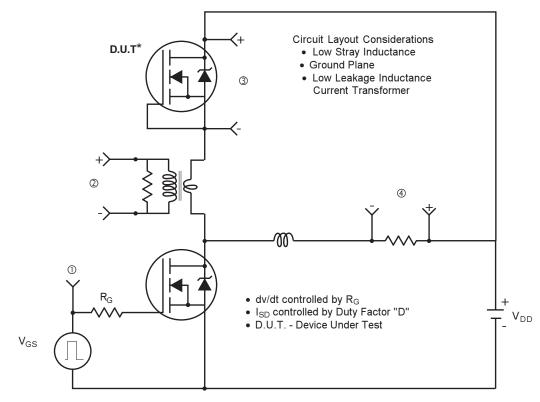
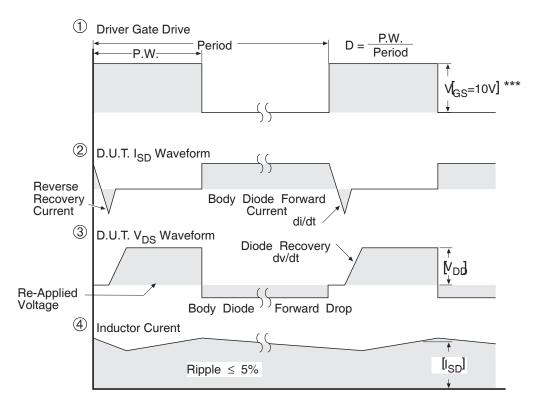


Fig 13b. Gate Charge Test Circuit



Peak Diode Recovery dv/dt Test Circuit

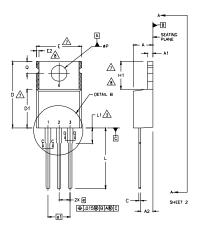
* Reverse Polarity of D.U.T for P-Channel

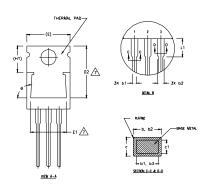


*** $V_{\rm GS}$ = 5.0V for Logic Level and 3V Drive Devices

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)





NOTES	3:	
1 2 3 4	DIVENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994. DIVENSIONS ARE SHOWN IN INCHES [MILLIWETERS]. LEAD DIVENSION AND FINISH UNCONTROLLED IN L1. DIVENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIVENSIONS ARE	LEAD ASSIGNM
$\overbrace{\frac{5}{6}}{7}$	SHALL NUT EXCELD JOUS (U.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERWOST EXTREMES OF THE PLASTIC BODY. DIMENSION 61 & c1 APPLY TO BASE METAL ONLY. CONTROLLING DIMENSION : INCHES. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1	<u>HEXFET</u> 1.– GATE 2.– DRAI 3.– SOUI
8	DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARTIES ARE ALLOWED.	<u>IGBTS, Copa</u> 1 gate 2 coli 3 emit

SYMBOL	MILLIM	ETERS	INC	HES	
	Min.	MAX.	MIN.	MAX.	NOTES
Α	3.56	4.82	.140	.190	
A1	0,51	1,40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1,15	1,77	.045	.070	
b3	1,15	1.73	.045	.068	
с	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12,19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
е	2.54 5,	BSC	.100	.100 BSC .200 BSC	
e1					
H1	5,85	6,55	.230	.270	7,8
L	12.70	14,73	.500	,580	
L1	-	6,35	-	.250	3
øР	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
ø	90*-	-93'	90'-	90'-93'	
			I		

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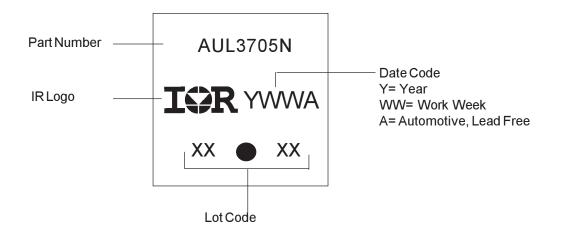
TIEXTER							
2	gate Drain Source						

PACK LLECTOR

DIODES

1.- ANODE/OPEN 2.- CATHODE 3.- ANODE

TO-220AB Part Marking Information





Ordering Information

Base part	Package Type	Standard Pack	Complete Part Number	
		Form	Quantity	
AUIRL3705N	TO-220	Tube	50	AUIRL3705N

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